



EMI Parameters for IBIS

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Proposed EMI parameters

- Cpd
Power Dissipation Capacitance.
 - This is the internal parasitic capacitance + the equivalent capacitance associated with the *through currents* when both transistors are momentarily conducting.
 - Parameter is given in the datasheets.
 - Used to calculate the noise voltage on the power bus ($I(t) = C_{eff} dv/dt$ where C_{eff} is the total decoupling capacitance).
- DIE HEIGHT
Represented by package thickness.
 - Used for loop area calculation.

Proposed EMI parameters

- **HEATSINK**

Heatsink dimensions (Length, Width, Thickness).

Dimensions used to calculate capacitance.

Also need to indicate which components have a heatsink.

Heatsinks can act as antennas and are driven by potential differences on the power plane.

- **CON_PIN**

Assigns a model name to a pin of a connector.

- **CON_SPEC**

Assigns parameters to CON_PIN. Parameters indicate whether the pin is unshielded, shielded, connected to the shield, has a ferrite filter, and has an explicit filter capacitor.

Used to calculate an antenna impedance for the pin.

Proposed EMI parameters - examples

- Example 1

[Component] comp_1
CPD 6.4 # pF
ICCD 61.5 # mA/MHz

- Example 2

[Component] comp_2
DIE_HEIGHT 78.74 # mils
HEATSINK L: 590.55 W: 590.55 T: 472:44 # mils

Proposed EMI parameters - examples

- Example 3

[Component] connector_1

CON_PIN 1 sig_out

CON_PIN 2 sig_shield

CON_PIN 3 sig_out

CON_PIN G1 grounded

[Model] sig_out

CON_SPEC unshielded C: 6.0 # unshielded pin, C in pF

[Model] sig_shield

CON_SPEC is_to_shield C: 9.0 # pin connected to the shielded, C in pF

[Model] grounded

CON_SPEC is_shielded C: 7.0 # individually shielded pin, C in pF

What's next?

- Use proper SI units
E.g. e-12F instead of pF, Metric units, etc.
- Prepare a more detailed specification
 - Need to add more details as to why these parameters are important.
 - How to measure the parameters.
- Submit a Bird